AMENDMENTS TO THE CLAIMS

The listing of claims replaces all prior versions, and listings, of claims in the application:

Listing of Claims

1-11. (Cancelled)

12. (Currently amended) An arrangement for contacting terminals of a substrate comprising a substrate surface, a first terminal having a first terminal surface, and a second terminal having a second terminal surface, the first terminal surface being located at a shorter distance from the substrate surface than the second terminal surface, the arrangement comprising:

a first insulating layer on the substrate surface, having an insulation-layer surface being located at a longer distance from the substrate surface than the second terminal surface, wherein a part of said first insulating layer is arranged between the first and the second terminal;

a second insulating layer arranged on the first insulating layer;

wherein the first insulating layer has a contact via which extends from the insulation-layer surface to the first terminal surface and is filled with a first conductive material, and wherein the second insulating layer has a recess, said recess penetrating the second insulating layer and ~~former,~~ extending [[~~up~~]] to the first conductive material and into the first dielectric layer[[~~,~~]] and being filled with a second conductive material, such that the second conductive material contacts the first conductive material on a top surface

and on a portion of a side surface thereof; and

wherein a recess extends to the second terminal surface through the first and second insulating layers, and is filled with a third conductive material.

13. (Previously presented) The arrangement as claimed in claim 12, wherein the first terminal is one of a base terminal and a collector terminal, and the second terminal is an emitter terminal, arranged on a stack, of a bipolar transistor.

14. (Previously presented) The arrangement as claimed in claim 12, wherein the first terminal is one of a source terminal and a drain terminal, and the second terminal is a gate terminal of a field-effect transistor.

15. (Previously presented) The arrangement as claimed in claim 12, wherein the first terminal is formed on the substrate and is selected from the group of a base terminal of a bipolar transistor, a collector terminal of a bipolar transistor, a gate terminal of a field-effect transistor, a source terminal of a field-effect transistor and a drain terminal of a field-effect transistor.

16. (Previously presented) The arrangement as claimed in claim 12, wherein at least one of the first conductive material, the second conductive material and the third conductive material comprises metal.

17. (Original) The arrangement as claimed in claim 12, wherein the first conductive

material is tungsten.

18. (Previously presented) The arrangement as claimed in claim 12, wherein at least one of the second and third conductive materials is copper.

19. (Original) The arrangement as claimed in claim 12, wherein the second conductive material is conductively connected to the first conductive material and forms a first contact terminal, and wherein the third conductive material is conductively connected to the second terminal and forms a second contact terminal.

20. (Original) The arrangement as claimed in claim 12, wherein the first and second contact terminals form a wiring plane.